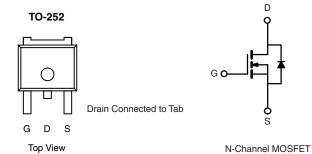


www.vishay.com

Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | |
|--|--------|--|--|--|
| V _{DS} (V) | 60 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.022 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$ | 0.033 | | | |
| I _D (A) | 25 | | | |
| Configuration | Single | | | |



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- 100 % R_g and UIS Tested
- AEC-Q101 Qualified^d
- Compliant to RoHS Directive 2002/95/EC



| ORDERING INFORMATION | |
|---------------------------------|------------------|
| Package | TO-252 |
| Lead (Pb)-free and Halogen-free | SQD25N06-22L-GE3 |

| ABSOLUTE MAXIMUM RATING | S ($T_C = 25$ °C, unles | s otherwise noted | d) | |
|---|-------------------------------------|-----------------------------------|---------------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | | V_{DS} | 60 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | |
| Continuous Drain Current | T _C = 25 °C ^a | 1 | 25 | |
| | T _C = 125 °C | - I _D | 20 | |
| Continuous Source Current (Diode Conduction) ^a | | Is | 25 | А |
| Pulsed Drain Currentb | | I _{DM} | 100 | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 24 | |
| Single Pulse Avalanche Energy | L = U.1 IIII | E _{AS} | 28 | mJ |
| Maximum Power Dissipation ^b | T _C = 25 °C | D | 62 | 10/ |
| | T _C = 125 °C | P_{D} | 20 | W |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to + 175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|------------------------|------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-Ambient | PCB Mount ^c | R_{thJA} | 50 | °C/W | |
| Junction-to-Case (Drain) | | R_{thJC} | 2.4 | C/VV | |

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (Fr-4 material).
- d. Parametric verification ongoing.



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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT | |
|---|--------------------------|--|---|------|-------|-------|------|--|
| Static | | | | l | | ı | | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$ | | 60 | | - | V | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | | 2.0 | 2.5 | | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | - | ± 100 | nA | |
| | | V _{GS} = 0 V | V _{DS} = 60 V | - | - | 1.0 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 125 °C | - | - | 50 | μA | |
| | | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 175 °C | - | - | 250 | | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 25 | - | - | Α | |
| | | V _{GS} = 10 V | I _D = 20 A | =. | 0.018 | 0.022 | Ω | |
| Drain-Source On-State Resistance ^a | | V _{GS} = 10 V | I _D = 20 A, T _J = 125 °C | =. | - | 0.039 | | |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} = 10 V | I _D = 20 A, T _J = 175 °C | - | - | 0.049 | | |
| | | V _{GS} = 4.5 V | I _D = 20 A, T _J = 25 °C | =. | 0.027 | 0.033 | | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 15 V, I _D = 12 A | | =. | 32 | - | S | |
| Dynamic ^b | · | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 1580 | 1975 | pF | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ $V_{DS} = 25 V$ | $V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$ | - | 305 | 382 | | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 130 | 163 | | |
| Total Gate Charge ^c | Qg | | | - | 33 | 50 | | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 30 \text{ V}, I_{D} = 25 \text{ A}$ | =. | 5.3 | - | nC | |
| Gate-Drain Charge ^c | Q _{gd} | | | - | 6.8 | - | | |
| Gate Resistance | R _g | f = 1 MHz | | 1.1 | 2.2 | 3.3 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | =. | 8 | 12 | | |
| Rise Time ^c | t _r | V_{DD} = 30 V, R_L = 1.2 Ω $I_D \cong$ 25 A, V_{GEN} = 10 V, R_g = 1 Ω | | =. | 10 | 15 | ns | |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 24 | 36 | | |
| Fall Time ^c | t _f | | | - | 6 | 9 | | |
| Source-Drain Diode Ratings and Char | acteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | = | 100 | Α | |
| Forward Voltage | V _{SD} | I _F = 25 A, V _{GS} = 0 V | | - | 0.9 | 1.5 | V | |

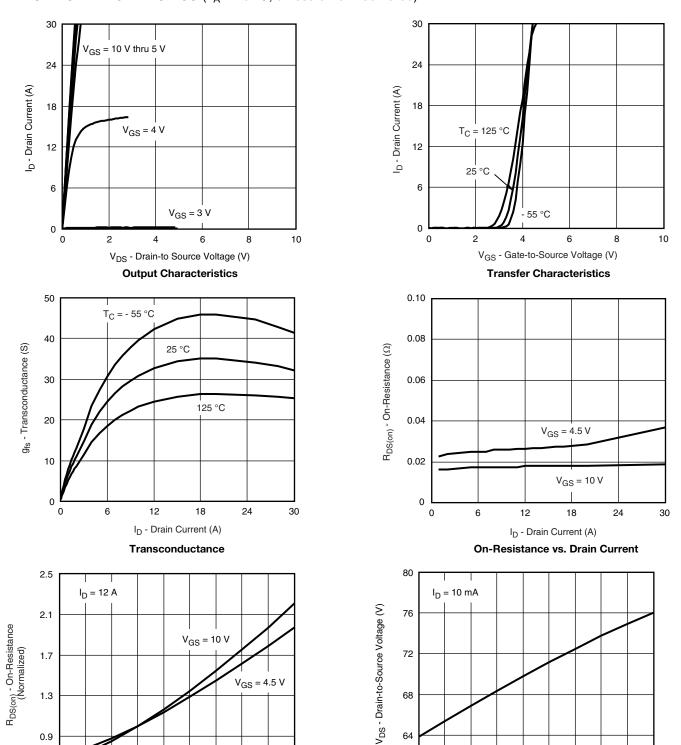
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



T_{.1} - Junction Temperature (°C) On-Resistance vs. Junction Temperature

50

75

100 125 150

0.9

0.5

- 50

- 25

0 25 75

100 125 150 175

25

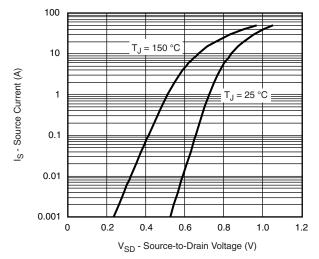
64

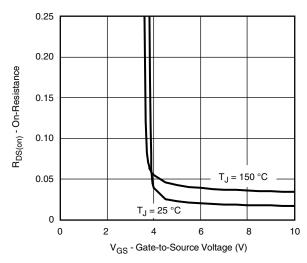
60

- 50 - 25

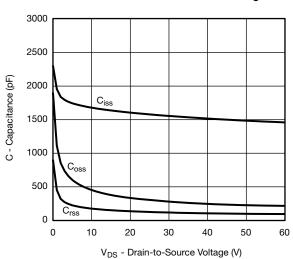


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

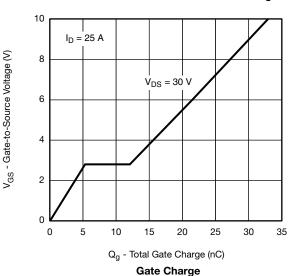




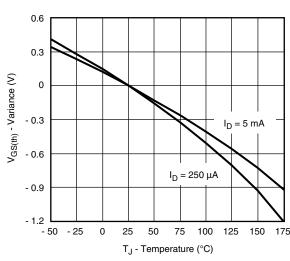
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



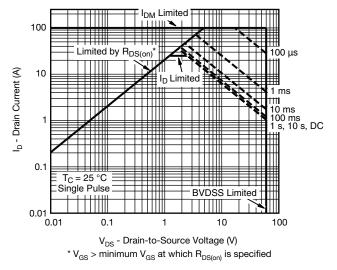
Capacitance



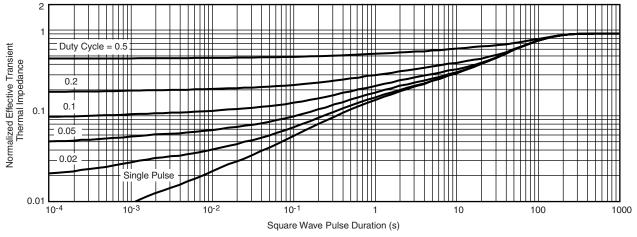
Threshold Voltage



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



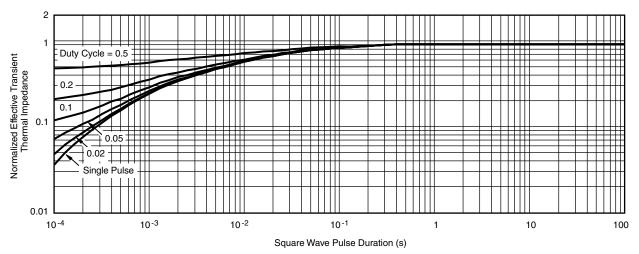
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- · The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg265360.



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TO-252AA Case Outline





| | MILLIN | METERS | INC | HES |
|---------------------------------|----------|--------|-----------|-------|
| DIM. | MIN. | MAX. | MIN. | MAX. |
| Α | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| С | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 4.10 | - | 0.161 | - |
| Е | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| Н | 9.40 | 10.41 | 0.370 | 0.410 |
| е | 2.28 | BSC | 0.090 | BSC |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.01 | 1.52 | 0.040 | 0.060 |
| ECN: T13-0592-Rev. A, 02-Sep-13 | | | | |

DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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